

Features

- Dual N-Channel MOSFET
- Low On-Resistance
 - 100mΩ @ V_{GS} = 4.5V, I_D = 2.5A
 - 140mΩ @ V_{GS} = 2.5V, I_D = 1.5A
 - 215mΩ @ V_{GS} = 1.8V, I_D = 1A
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate to 2kV HBM
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

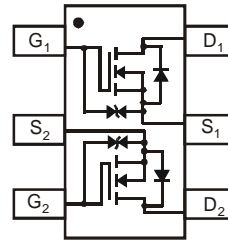


ESD PROTECTED TO 2KV



TOP VIEW

SOT-26



TOP VIEW

Schematic and Pin Configuration

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.015 grams (approximate)

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±12	V
Drain Current (Note 1)	I _D	T _A = 25°C	2.0
		T _A = 85°C	1.4
Pulsed Drain Current (Note 4)	I _{DM}	7.0	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P _D	650	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	192	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB, or minimum recommended pad layout
 2. No purposefully added lead.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 4. Pulse width ≤ 10μs, duty cycle ≤ 1%.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	0.6	—	1.0	V	V _{DS} = V _{CS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	80	100	mΩ	V _{GS} = 4.5V, I _D = 2.5A
			105	140		V _{GS} = 2.5V, I _D = 1.5A
			165	215		V _{GS} = 1.8V, I _D = 1.0A
Forward Transfer Admittance	Y _{fs}	—	5	—	S	V _{DS} = 5V, I _D = 2.4A
Diode Forward Voltage (Note 5)	V _{SD}	—	0.73	1.1	V	V _{GS} = 0V, I _S = 1.05A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	188	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	44	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	30	—	pF	
Turn-On Delay Time	t _{d(on)}	—	8	—	ns	V _{DD} = 10V, R _L = 10Ω I _D = 1A, V _{GEN} = 4.5V, R _G = 6Ω
Rise Time	t _r	—	3.8	—		
Turn-Off Delay Time	t _{d(off)}	—	19.6	—		
Fall Time	t _f	—	8.3	—		

Notes: 5. Short duration pulse test used to minimize self-heating effect.

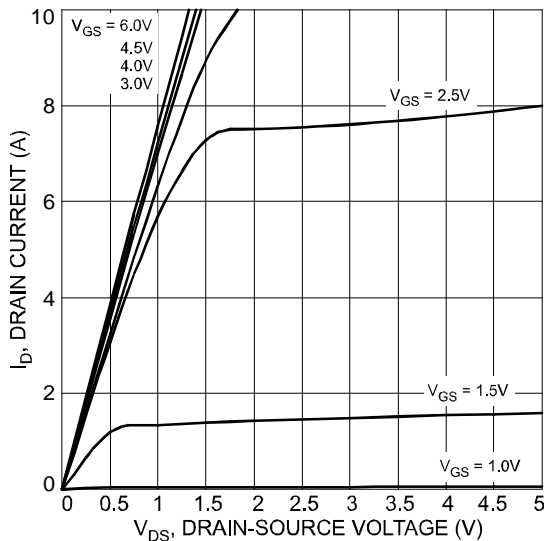


Fig. 1 Typical Output Characteristic

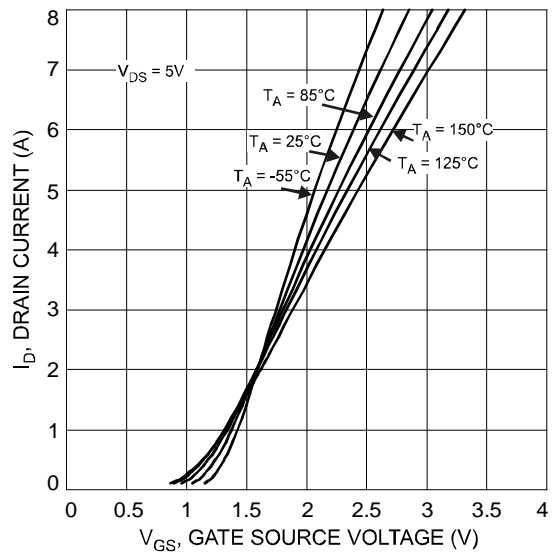


Fig. 2 Typical Transfer Characteristics

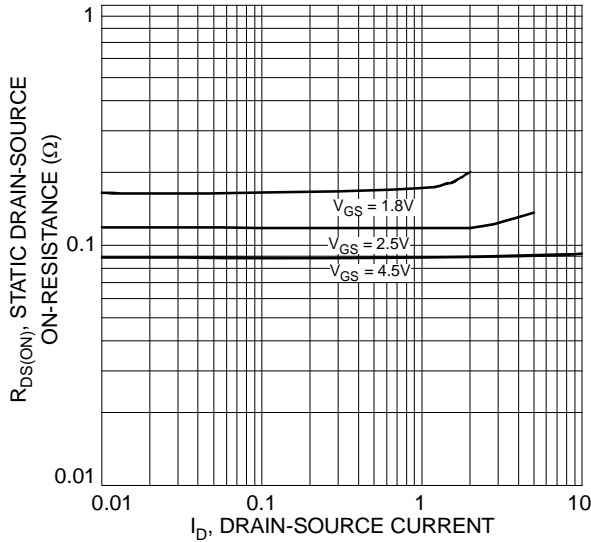


Fig. 3 On-Resistance vs. Drain-Source Current & Gate Voltage

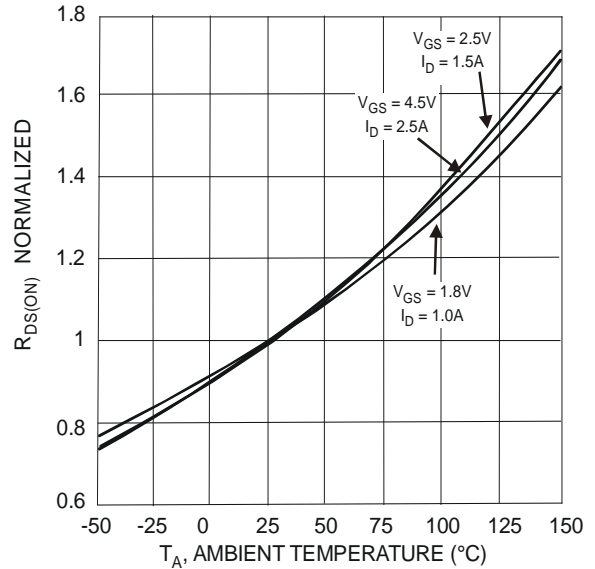


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

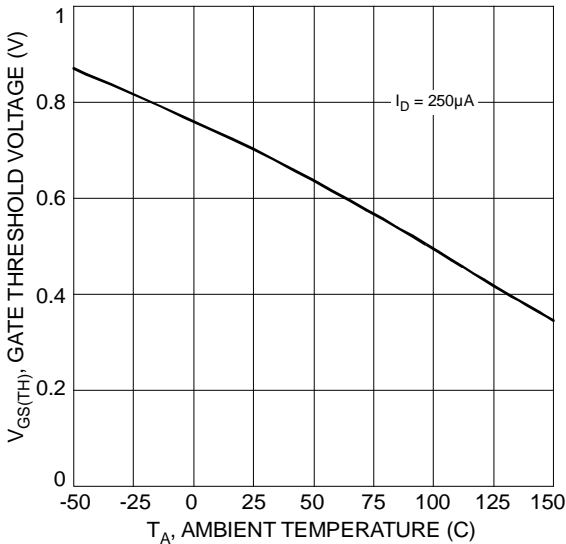


Fig. 5 Gate Threshold Variation with Temperature

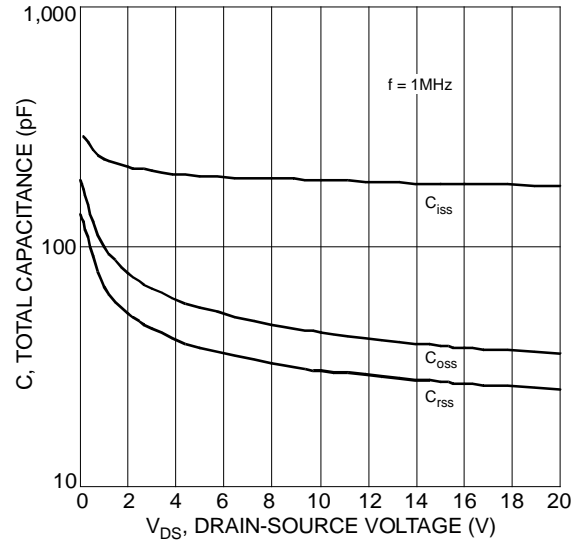


Fig. 6 Typical Total Capacitance

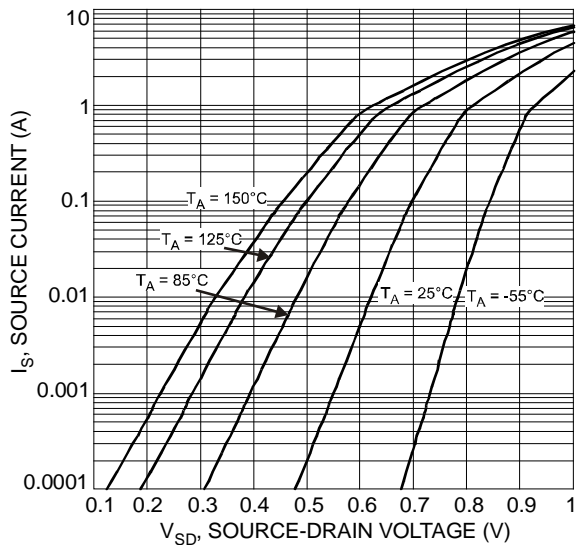
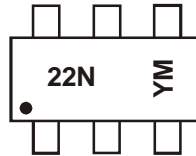


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

Ordering Information (Note 6)

Part Number	Case	Packaging
DMN2215UDM-7	SOT-26	3000/Tape & Reel

 Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

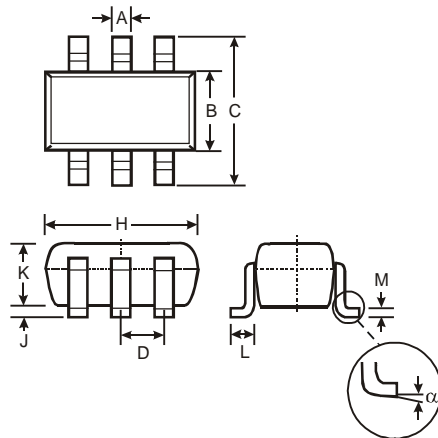
Marking Information


22N = Marking Code
 YM = Date Code Marking
 Y = Year ex: U = 2007
 M = Month ex: 9 = September

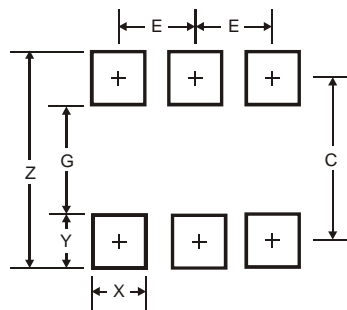
Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	U	V	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions


SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout


Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C	2.40
E	0.95

IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.